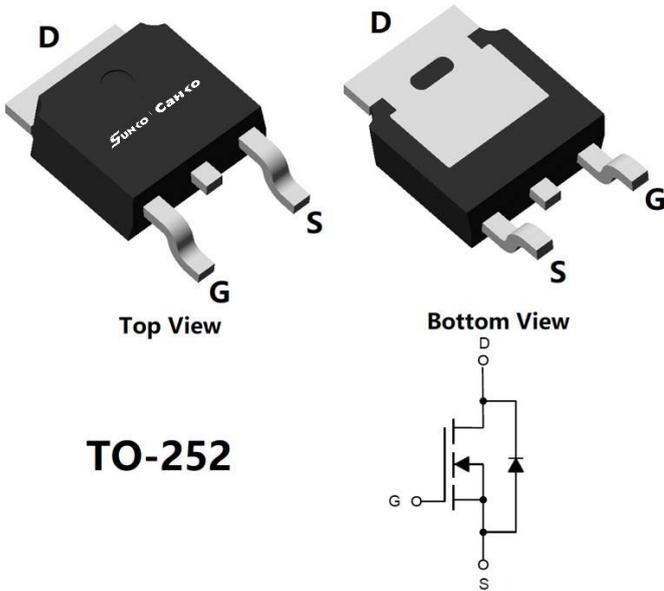


N-Channel Enhancement Mode Field Effect Transistor



TO-252

Product Summary

- V_{DS} 100V
- I_D 45A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <17 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <21.5 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|-------------------|------------|
| Drain-source Voltage | V_{DS} | 100 | V |
| Gate-source Voltage | V_{GS} | ± 20 | V |
| Drain Current | I_D | $T_C=25^\circ C$ | 45 |
| | | $T_C=100^\circ C$ | 28.5 |
| Pulsed Drain Current ^A | I_{DM} | 180 | A |
| Avalanche energy ^B | EAS | 81 | mJ |
| Total Power Dissipation ^C | P_D | $T_C=25^\circ C$ | 72 |
| | | $T_C=100^\circ C$ | 28.8 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55~+150 | $^\circ C$ |

■ Thermal resistance

| Parameter | Symbol | Typ | Max | Units |
|---|-----------------|--------------|-----|--------------|
| Thermal Resistance Junction-to-Ambient ^D | $R_{\theta JA}$ | 15 | 20 | $^\circ C/W$ |
| Thermal Resistance Junction-to-Ambient ^D | | Steady-State | 40 | |
| Thermal Resistance Junction-to-Case | $R_{\theta JC}$ | 1.35 | 1.7 | |

■ Ordering Information (Example)

| PREFERRED P/N | PACKING CODE | Marking | MINIMUM PACKAGE(pcs) | INNER BOX QUANTITY(pcs) | OUTER CARTON QUANTITY(pcs) | DELIVERY MODE |
|---------------|--------------|-----------|----------------------|-------------------------|----------------------------|---------------|
| SCD45G10A | F1/F2 | SCD45G10A | 2500 | / | 25000 | 13"Reel |

■ Electrical Characteristics (T_j=25°C unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Units |
|---------------------------------------|---------------------|---|-----|------|------|-------|
| Static Parameter | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} = 0V, I _D =250μA | 100 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =100V, V _{GS} =0V | | | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} = ±20V, V _{DS} =0V | | | ±100 | nA |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D =250μA | 1 | 1.8 | 3 | V |
| Static Drain-Source On-Resistance | R _{DS(on)} | V _{GS} = 10V, I _D =20A | | 14 | 17 | mΩ |
| | | V _{GS} = 4.5V, I _D =20A | | 17 | 21.5 | mΩ |
| Diode Forward Voltage | V _{SD} | I _S =20A, V _{GS} =0V | | | 1.3 | V |
| Maximum Body-Diode Continuous Current | I _S | | | | 45 | A |
| Gate resistance | R _G | f= 1 MHz, Open drain | | 1 | | Ω |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =50V, V _{GS} =0V, f=1MHZ | | 1135 | | pF |
| Output Capacitance | C _{oss} | | | 399 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 18 | | |
| Switching Parameters | | | | | | |
| Total Gate Charge | Q _g | V _{GS} =10V, V _{DS} =50V, I _D =25A | | 16 | | nC |
| Gate-Source Charge | Q _{gs} | | | 5.6 | | |
| Gate-Drain Charge | Q _{gd} | | | 2.4 | | |
| Reverse Recovery Chrage | Q _{rr} | I _F =20A, di/dt=100A/us | | 42 | | ns |
| Reverse Recovery Time | t _{rr} | | | 39.8 | | |
| Turn-on Delay Time | t _{D(on)} | V _{GS} =10V, V _{DD} =50V, I _D =25A R _{GEN} =2.2Ω | | 39.2 | | ns |
| Turn-on Rise Time | t _r | | | 11 | | |
| Turn-off Delay Time | t _{D(off)} | | | 53.2 | | |
| Turn-off fall Time | t _f | | | 15.8 | | |

A. Repetitive rating; pulse width limited by max. junction temperature.

B. V_{DD}=50V, V_{GS}=10V, L=5mH, I_{AS}=5.7A.

C. Pd is based on max. junction temperature, using junction-case thermal resistance.

D. The value of RqJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C. The Power dissipation PDSM is based on R qJA t ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

■ Typical Performance Characteristics

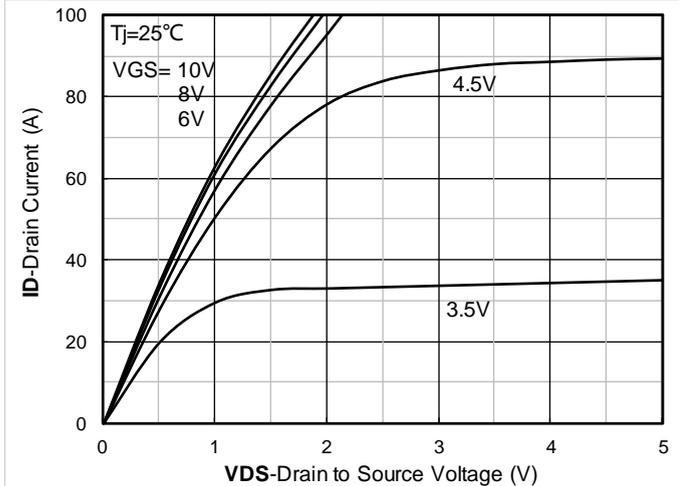


Figure1. Output Characteristics

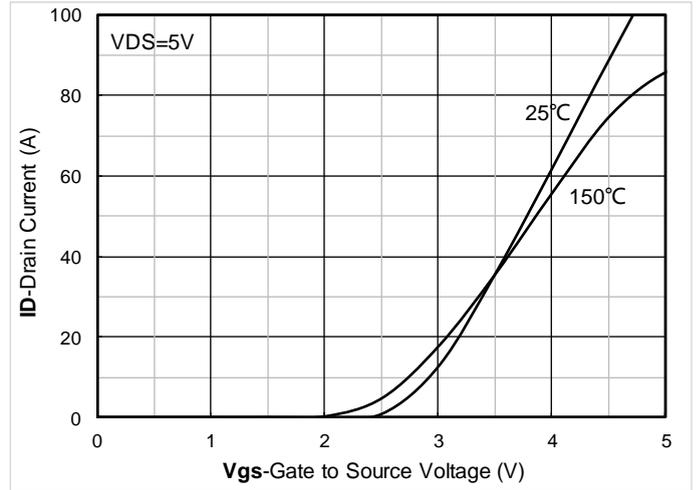


Figure2. Transfer Characteristics

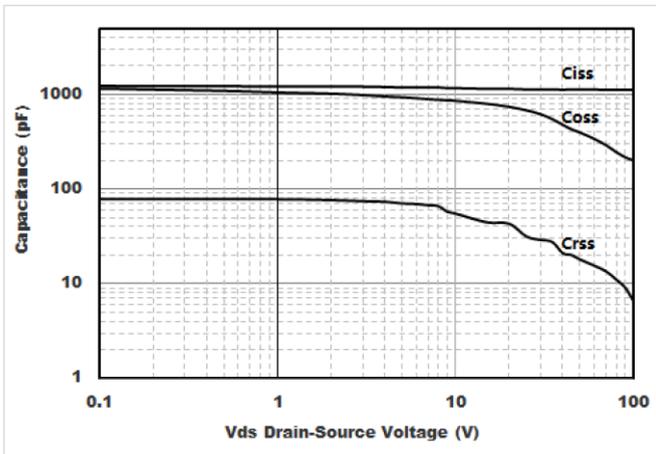


Figure3. Capacitance Characteristics

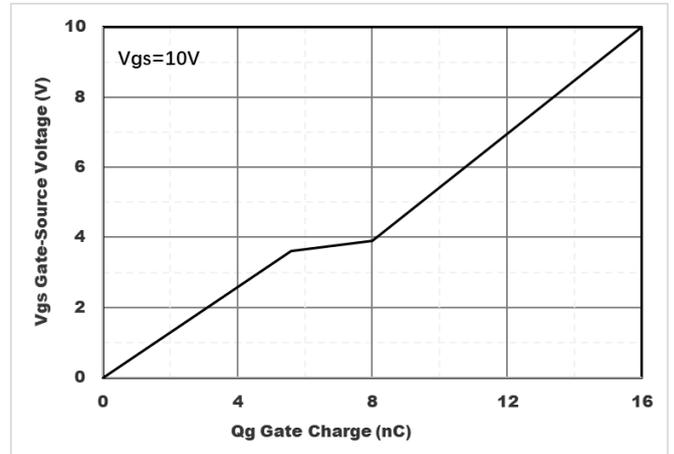


Figure4. Gate Charge

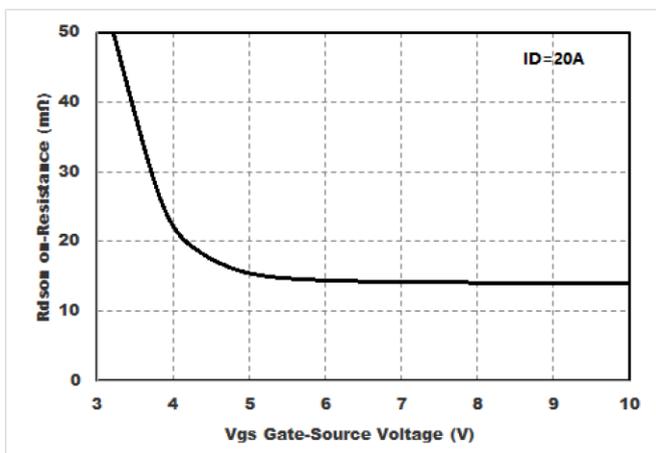


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

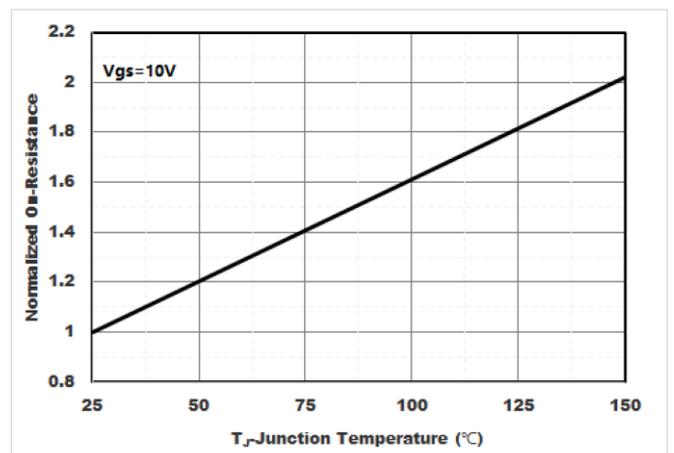


Figure6. Normalized On-Resistance

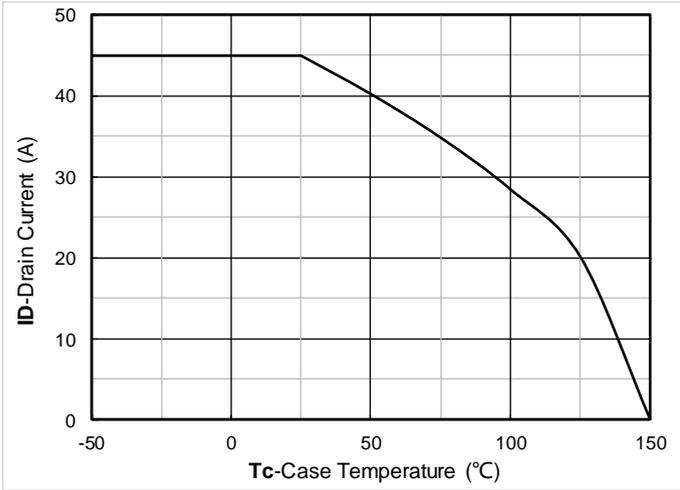


Figure7. Drain current

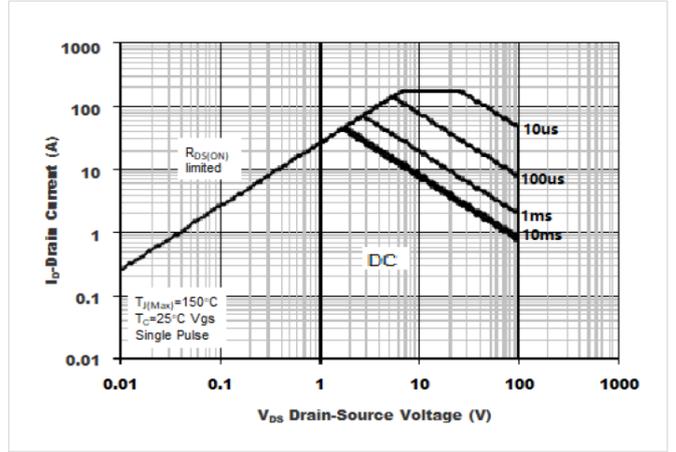


Figure8.Safe Operation Area

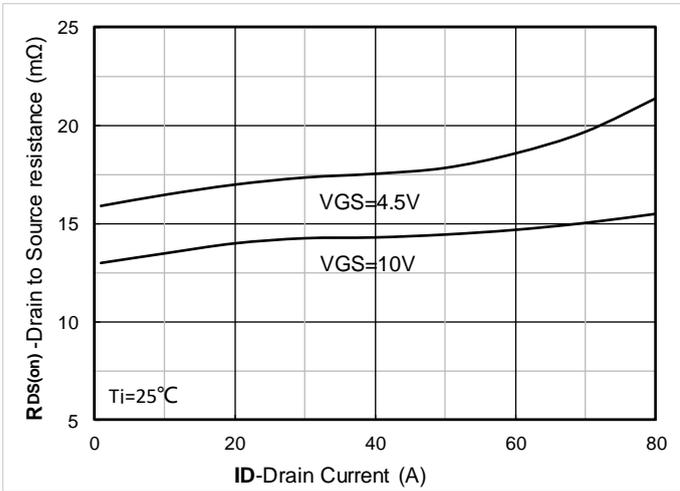


Figure 9. RDS(on) VS Drain Current

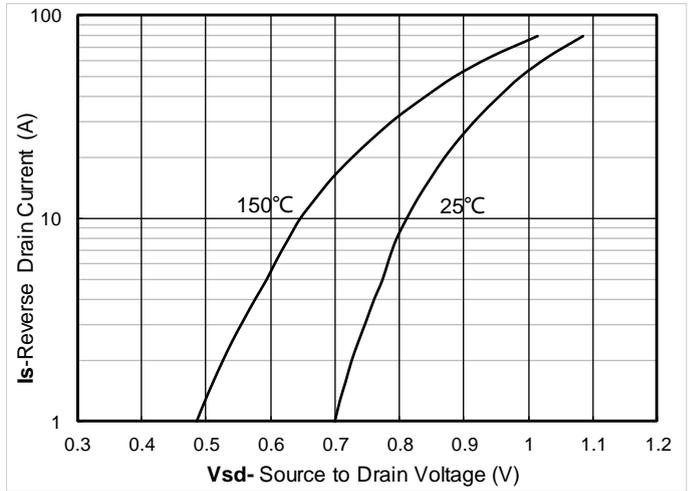


Figure 10. Forward characteristics of reverse diode

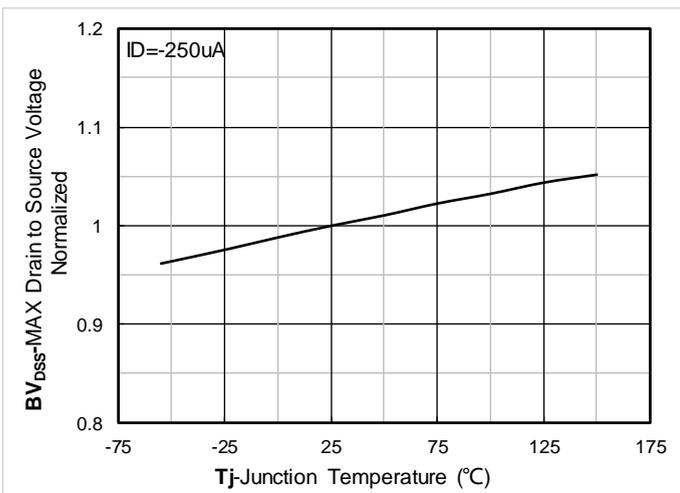


Figure 11. Normalized breakdown voltage

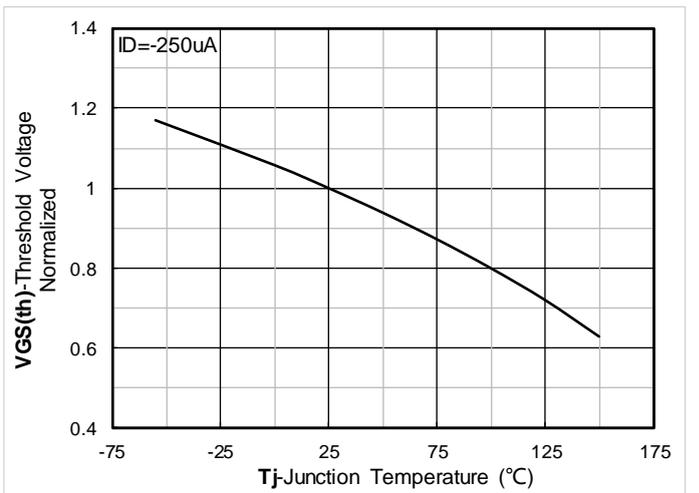


Figure 12. Normalized Threshold voltage

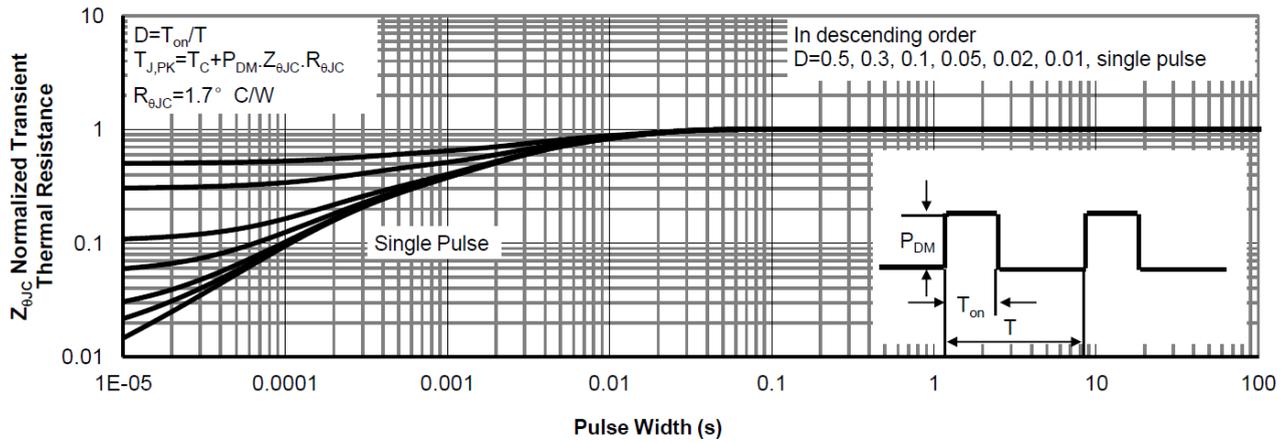
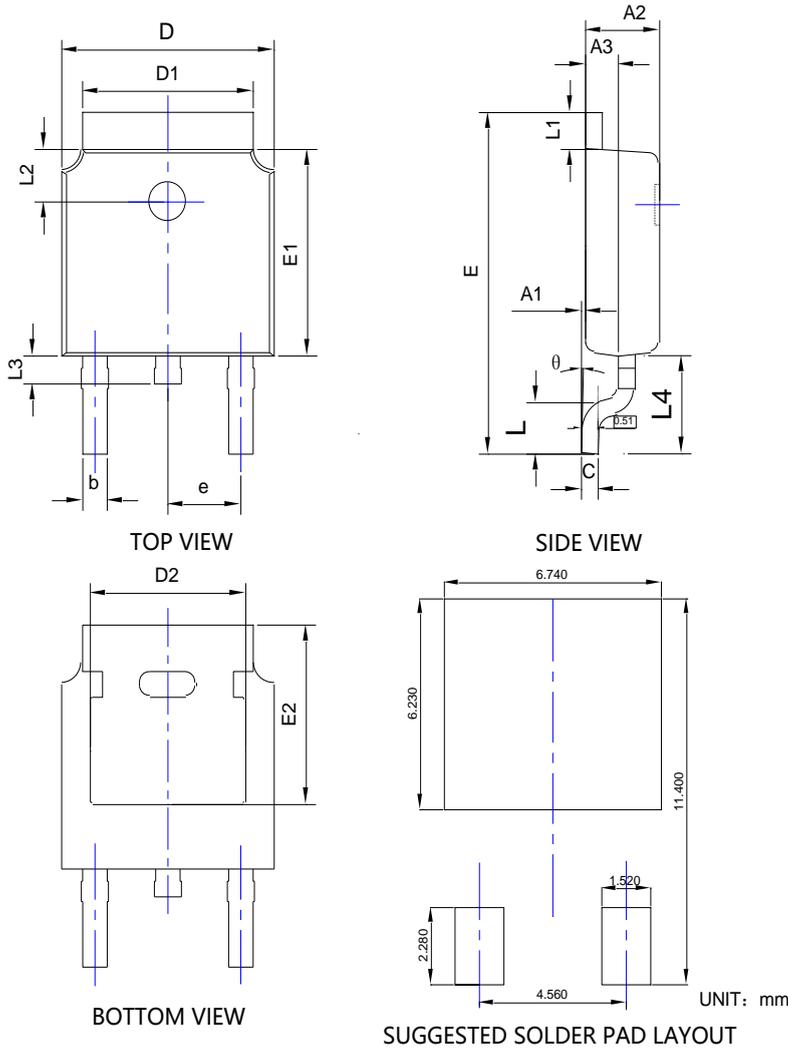


Figure13.Normalized Maximum Transient thermal impedance

■ TO-252-B Package information



| SYMBOL | DIMENSIONS | | | | | |
|--------|------------|-------|-------|------------|--------|--------|
| | INCHES | | | Millimeter | | |
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A1 | 0.000 | --- | 0.008 | 0.000 | --- | 0.200 |
| A2 | 0.087 | 0.091 | 0.094 | 2.200 | 2.300 | 2.400 |
| A3 | 0.035 | 0.039 | 0.043 | 0.900 | 1.000 | 1.100 |
| b | 0.026 | 0.030 | 0.034 | 0.660 | 0.760 | 0.860 |
| c | 0.018 | 0.020 | 0.023 | 0.460 | 0.520 | 0.580 |
| D | 0.256 | 0.260 | 0.264 | 6.500 | 6.600 | 6.700 |
| D1 | 0.203 | 0.209 | 0.215 | 5.150 | 5.300 | 5.450 |
| D2 | 0.181 | 0.189 | 0.195 | 4.600 | 4.800 | 4.950 |
| E | 0.390 | 0.398 | 0.406 | 9.900 | 10.100 | 10.300 |
| E1 | 0.236 | 0.240 | 0.244 | 6.000 | 6.100 | 6.200 |
| E2 | 0.203 | 0.209 | 0.215 | 5.150 | 5.300 | 5.450 |
| e | 0.090BSC | | | 2.286BSC | | |
| L | 0.049 | 0.059 | 0.069 | 1.250 | 1.500 | 1.750 |
| L1 | 0.035 | --- | 0.050 | 0.900 | --- | 1.270 |
| L2 | 0.055 | --- | 0.075 | 1.400 | --- | 1.900 |
| L3 | 0.024 | 0.031 | 0.039 | 0.600 | 0.800 | 1.000 |
| L4 | 0.114REF | | | 2.900REF | | |
| θ | 0° | --- | 10° | 0° | --- | 10° |

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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